

FORM 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)	Docket Number: 10873.1384US01	Application Number: 10/758815
	Applicant: KITAOKA, et al.	
	Filing Date: January 16, 2004	Group Art Unit: 2813

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
/SM/	3,811,963	May, 1974	Hawrylo, et al.			
/SM/	3,933,538	January, 1976	Akai, et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
/SM/	57-78132	May, 1982	Japan			Abstract	
/SM/	0 967 664	December, 1999	EPO				
/SM/	1 184 897	March, 2002	EPO				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

/SM/		Gavrilin, et al., "Liquid-Phase Epitaxy of Gallium Nitride from Lithium-Gallium Melts", Journal of Advanced Materials, vol. 5, no. 2, pp. 21-25, 2000
/SM/		Aoki, et al., "Growth of 5 mm GaN Single Crystals at 750°C from an Na-Ga Melt", Crystal Growth & Design, vol. 1, no. 2, pp. 119-122, 2001

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EXAMINER	/Sonya Mccall Shepard/	DATE CONSIDERED	12/19/2007
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.